



Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, CA 90638
 Phone: (562) 404-4474 * Fax: (562) 404-1773
 ssdi@ssdi-power.com * www.ssdi-power.com

SFT6678 SERIES

**15 AMPS
 400 Volts
 NPN High Speed
 Power Transistor**

DESIGNER'S DATA SHEET

Part Number / Ordering Information ^{1/}

SFT6678 **M** **TX**

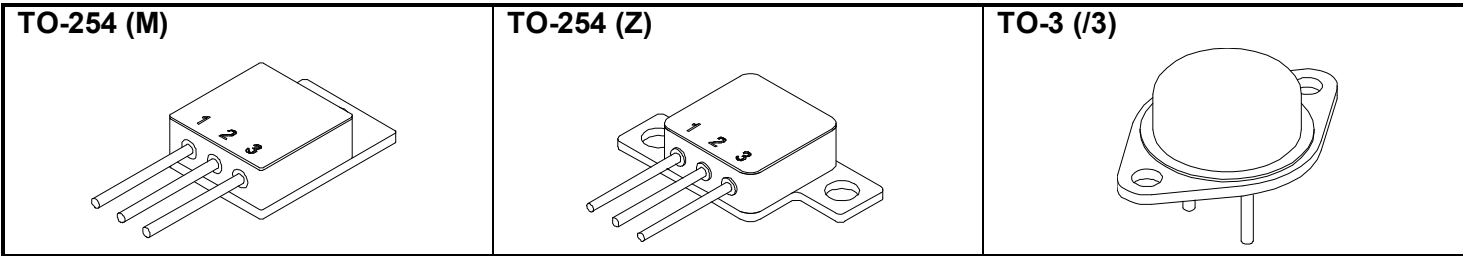
Screening ^{2/} = Not Screened
 TX = TX Level
 TXV = TXV Level
 S = S Level

Lead Bend ^{3/} = Straight Leads
 UB = Up Bend
 DB = Down Bend

Package M = TO-254
 Z = TO-254Z
 /3 = TO-3

- Application Notes:**
- Replaces Industry Standard 2N6678
 - Designed for High Voltage, High Speed, Power Switching Applications Such as:
 - Off-Line Supplies
 - Converter Circuits
 - Pulse Width Modulated Regulators
 - Motor Controls
 - Deflection Circuits

Maximum Ratings	Symbol	Value	Units
Collector – Emitter Voltage	V _{CEO}	400	Volts
Collector – Base Voltage	V _{CBO}	650	Volts
Emitter – Base Voltage	V _{EBO}	8.0	Volts
Continuous Collector Current	I _C	15	Amps
Continuous Base Current	I _B	5.0	Amps
Operating and Storage Temperature	T _J , T _{STG}	-65 to +200	°C
Total Power Dissipation @ T _C =25°C	P _D	175	W
@ T _A =25°C		6.0	W
Maximum Thermal Resistance (Junction to Case)	R _{θJC}	1.0	°C/W
(Ambient to Case)	R _{θJA}	29.17	



NOTES:

- * Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%
- 1/ For ordering information, price, and availability contact factory.
- 2/ Screening based on MIL-PRF-19500. Screening flows available on request.
- 3/ Up and down bend configurations available for M and Z (TO-254 and TO-254Z) packages only.
- 4/ All electrical characteristics @ 25°C, unless otherwise specified.



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Electrical Characteristics		Symbol	Min	Max	Units		
Collector Cutoff Current $V_{CE} = 400V, V_{BE(off)} = 1.5V$ $V_{CE} = 650V, V_{BE(off)} = 1.5V$ $V_{CE} = 650V, V_{BE(off)} = 1.5V$	$T_C = 25^\circ C$	I_{CEV}	-	0.5	μA		
	$T_C = 25^\circ C$			1.0	μA		
	$T_C = 125^\circ C$			50	μA		
Collector – Base Leakage Current	$V_{CB} = 650V$	I_{CBO}	-	1	mA		
Emitter Cutoff Current	$(V_{EB} = 8V, I_C = 0)$	I_{EBO}	-	2	mA		
Collector-Emitter Sustaining Voltage $(I_C = 200mA, I_B = 0)$		$V_{CEO(sus)}$	400	-	V		
DC Current Gain*	$V_{CE} = 3V, I_C = 15A, T_A = 25^\circ C$	H_{FE1}	8	20			
	$V_{CE} = 3V, I_C = 1A, T_A = 25^\circ C$	H_{FE2}	15	40			
	$V_{CE} = 3V, I_C = 15A, T_A = -55^\circ C$	H_{FE3}	4	-			
Base-Emitter Saturation Voltage* $(I_C = 15A, I_B = 3A)$		$V_{BE(SAT)}$	-	1.5	V		
Collector-Emitter Saturation Voltage* $(I_C = 15A, I_B = 3A)$	$(T_C = 25^\circ C)$ $(T_C = 125^\circ C)$	$V_{CE(SAT)}$	-	1.0 2.0	V		
Current Gain $(I_C = 1A, V_{CE} = 10V, f = 5MHz)$		$ h_{FE} $	3	10			
Output Capacitance $(V_{CB} = 10V, f = 0.1MHz)$		C_{ob}	150	500	pF		
Delay Time	$(V_{CC} = 200V, I_C = 15A, I_{B1} = I_{B2} = 3A, t_p = 50 \mu sec, \text{Duty Cycle} \leq 2\%, V_B = 6V, R_L = 13.5\Omega)$ INPUT WAVEFORM SEE NOTE 1 OUTPUT WAVEFORM t_d AND t_r TIME TEST CIRCUIT	$t_{(on)}$	t_d	-	0.1	μsec	
Rise Time			t_r	-	2.5		
Storage Time		 INPUT WAVEFORM SEE NOTE 1 OUTPUT WAVEFORM t_s AND t_f TIME TEST CIRCUIT	$t_{(off)}$	t_s	-		0.6
Fall Time				t_f	-		0.5
Cross Over Time	$(I_C = 15 A(pk), V_{CLAMP} = 450V, I_{B1} = 3 A, V_{BE(off)} = 6V)$ OUTPUT WAVEFORM t_c TIME TEST CIRCUIT SAME INPUT WAVEFORM AS t_s AND t_f TIME TEST CIRCUIT	t_c	-	0.5	μsec		

NOTE: All specifications are subject to change without notification.
 SSD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0019D

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Safe Operating Area, DC

$V_{CE} = 11.7 \text{ V}, I_C = 15 \text{ A}, 1 \text{ sec}$

$V_{CE} = 30 \text{ V}, I_C = 5.9 \text{ A}, 1 \text{ sec}$

$V_{CE} = 100 \text{ V}, I_C = 0.25 \text{ A}, 1 \text{ sec}$

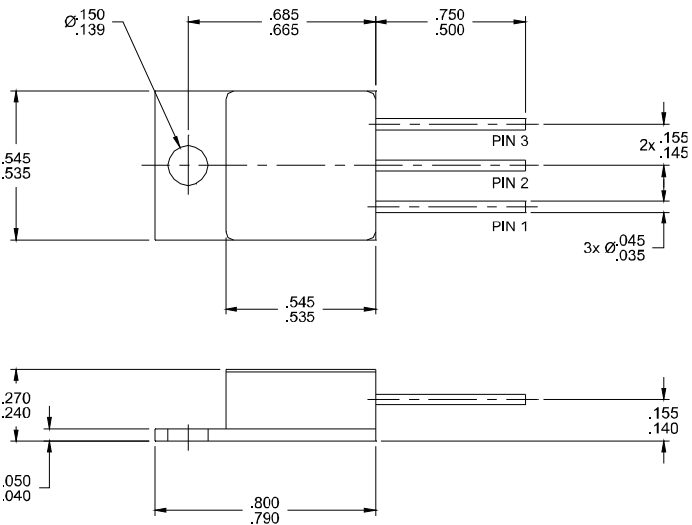
$V_{CE} = 400 \text{ V}, I_C = 10 \text{ mA}, 1 \text{ sec}$

Safe Operating Area, clamped switching

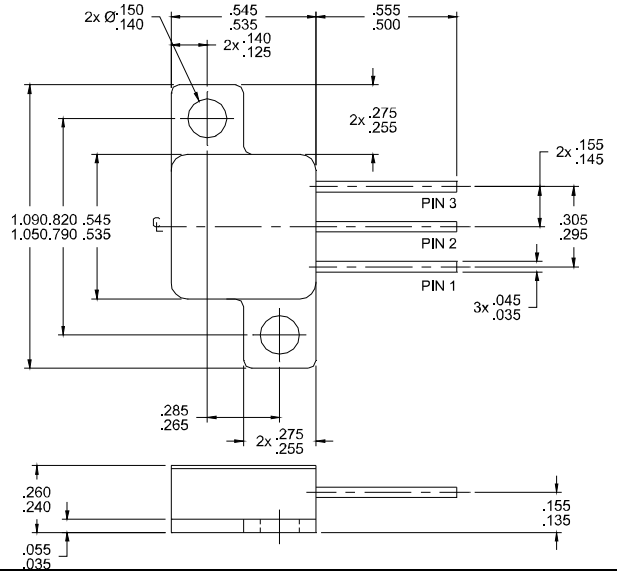
$V_{CC} = 15 \text{ V}, V_{BB2} = 5 \text{ V}, R_{BB1} = 5 \Omega, R_{BB2} = 1.5 \Omega, L = 50 \mu\text{H},$

$V_{\text{clamp}} = 450 \text{ V}, I_C = 15 \text{ A}$

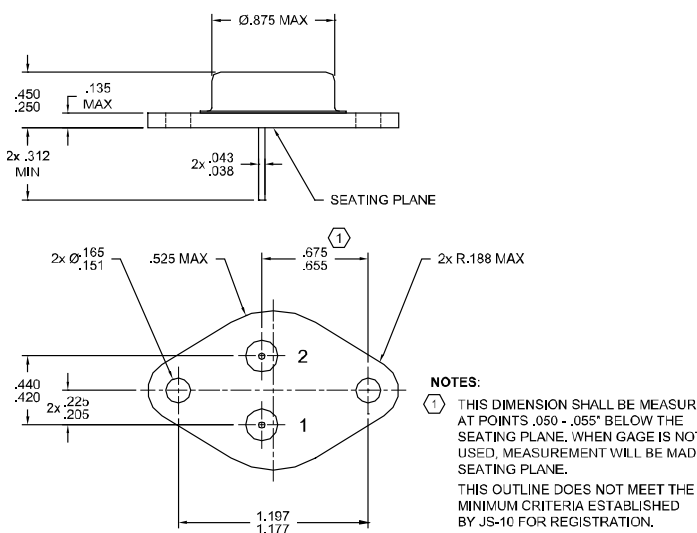
Case Outline: TO-254



Case Outline: TO-254Z



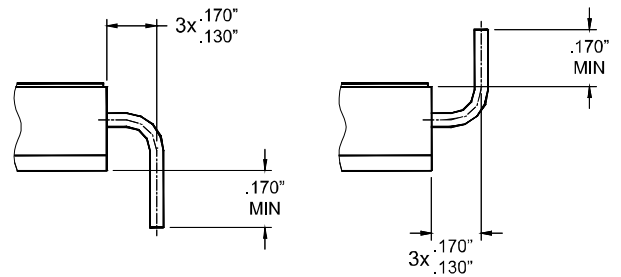
Case Outline: TO-3



Lead Options

DB (Down Bend)

UB (Up Bend)



PIN ASSIGNMENT (Standard)

Package	Collector	Emitter	Base
TO-3 (I3)	Case	Pin 2	Pin 3
TO-254 (M)	Pin 1	Pin 2	Pin 3
TO-254 (Z)	Pin 1	Pin 2	Pin 3

Available Part Numbers:

SFT6678/3	SFT6678M SFT6678MDB SFT6678MUB	SFT6678Z SFT6678ZDB SFT6678ZUB
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